## 502007051 07/30/2012

### PATENT ASSIGNMENT

## Electronic Version v1.1 Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

### **CONVEYING PARTY DATA**

Name	Execution Date
ANUP BHALLA	07/25/2012
HAMZA YILMAZ	07/26/2012
MADHUR BOBDE	07/25/2012
LINGPENG GUAN	07/27/2012
JUN HU	07/25/2012
JONGOH KIM	07/25/2012
YONGPING DING	07/25/2012

### **RECEIVING PARTY DATA**

Name:	Alpha and Omega Semiconductor Incorporated
Street Address:	475 Oakmead Pkwy
City:	Sunnyvale
State/Country:	CALIFORNIA
Postal Code:	94085

## PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	13561523

## **CORRESPONDENCE DATA**

 Fax Number:
 5106680239

 Phone:
 510.668.0965

 Email:
 josh@jdipatent.com

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent

via US Mail.

Correspondent Name: Joshua D. Isenberg
Address Line 1: 809 Corporate Way

Address Line 4: Fremont, CALIFORNIA 94539

ATTORNEY DOCKET NUMBER: ANO-056/US

PATENT
REEL: 028678 FRAME: 0058

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502007051

NAME OF SUBMITTER:	Joshua D. Isenberg
Total Attachments: 7 source=ANO-056_Assignment_signed#page source=ANO-056_Assignment_signed#page source=ANO-056_Assignment_signed#page source=ANO-056_Assignment_signed#page source=ANO-056_Assignment_signed#page source=ANO-056_Assignment_signed#page source=ANO-056_Assignment_signed#page	e2.tif e3.tif e4.tif e5.tif e6.tif

PATENT REEL: 028678 FRAME: 0059

# ASSIGNMENT

INVENTOR AND CITY	Whereas, I, ANUP BHALLA of 1406 Block Drive Santa Clara, CA 95050, USA
	have invented:
TITLE:	HIGH VOLTAGE FIELD BALANCE METAL OXIDE FIELD EFFECT TRANSISTOR (FBM)
DATE INVENTOR SIGNED THE DECLARATION	and executed a United States patent application therefor  on
	application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by
CITY AND	Signed and Sealed at Sunnyvale, CA
DATE	on Tuly 25th, 2012
	and bulla

Docket No.: ANO-056/US Assignment

Anup Bhalla

#### ASSIGNMENT

INVENTOR

Whereas, I, HAMZA YILMAZ of 20755 Trinity Avenue

AND CITY Saratoga, CA 95070, USA

have invented:

TITLE:

HIGH VOLTAGE FIELD BALANCE METAL OXIDE FIELD EFFECT TRANSISTOR (FBM)

SIGNED THE

DECLARATION

**DATE INVENTOR** and executed a United States patent application therefor

on 7/26, 2012. Said assignor hereby authorize and request their attorney, Joshua D. Isenberg, of 809 Corporate Way, Fremont, California, to insert here in parentheses (Application number 13/561,523 \_\_, filed \_\_ July 30, 2012 ) the filing date and application number of said application when known.

Whereas, Alpha and Omega Semiconductor Incorporated, a California Corporation, having its registered address at 475 Oakmead Pkwy, Sunnyvale, CA 94085, (hereinafter called **AOS**), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefore;

Now therefore for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the invention set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND

DATE

Hamza Yilmaz

Docket No.: ANO-056/US

Assignment

**PATENT** REEL: 028678 FRAME: 0061

### ASSIGNMENT

INVENTOR

Whereas, I, MADHUR BOBDE of 1602 Goldfinch Way

AND CITY

Sunnyvale CA 94087, USA

have invented:

TITLE:

HIGH VOLTAGE FIELD BALANCE METAL OXIDE FIELD

**EFFECT TRANSISTOR (FBM)** 

SIGNED THE DECLARATION

DATE INVENTOR and executed a United States patent application therefor

on Jwh 25th, 2012. Said assignor hereby authorize and request their attorney, Joshua D. Isenberg, of 809 Corporate Way, Fremont, California, to insert here in parentheses (Application number 13/561,523, filed July 30, 2012) the filing date and application number of said application when known.

Whereas, Alpha and Omega Semiconductor Incorporated, a California Corporation, having its registered address at 475 Oakmead Pkwy, Sunnyvale, CA 94085, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefore;

Now therefore for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the invention set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND

DATE

on July 25th, 2012

Madhur Bobde

Docket No.: ANO-056/US

Assignment

## ASSIGNMENT

INVENTOR AND CITY	Whereas, I, LINGPENG GUAN of 1428 Shaffer Drive San Jose, CA 95132, USA
	have invented:
TITLE:	HIGH VOLTAGE FIELD BALANCE METAL OXIDE FIELD EFFECT TRANSISTOR (FBM)
DATE INVENTOR SIGNED THE DECLARATION	and executed a United States patent application therefor  on
	Whereas, Alpha and Omega Semiconductor Incorporated, a California Corporation, having its registered address at 475 Oakmead Pkwy, Sunnyvale, CA 94085, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefore;
	Now therefore for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the invention set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by
CITY AND	Signed and Sealed at Sunggrale, $eA$ on $0.7(27)$ , 2012
DATE	on 07/27 ,2012
	Lingpeng Guan

Docket No.: ANO-056/US

PATENT REEL: 028678 FRAME: 0063

Assignment

### ASSIGNMENT

INVENTOR	
A NUES ACCUMENTS	

Whereas, I, JUN HU of 781 Acacia Avenue

AND CITY

San Bruno, CA 94066, USA

have invented:

TITLE:

HIGH VOLTAGE FIELD BALANCE METAL OXIDE FIELD

**EFFECT TRANSISTOR (FBM)** 

SIGNED THE

DECLARATION

**DATE INVENTOR** and executed a United States patent application therefor

on <u>07/25</u>, 2012. Said assignor hereby authorize and request their attorney, Joshua D. Isenberg, of 809 Corporate Way, Fremont, California, to insert here in parentheses (Application number 13/561,523 , filed July 30, 2012 ) the filing date and application number of said application when known.

Whereas, Alpha and Omega Semiconductor Incorporated, a California Corporation, having its registered address at 475 Oakmead Pkwy, Sunnyvale, CA 94085, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefore;

Now therefore for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the invention set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by

CITY AND

DATE

Signed and Sealed at Sanny whe, CA
on 7/25, 2012

Jun Hu

Docket No.: ANO-056/US

Assignment

**PATENT** REEL: 028678 FRAME: 0064

# ASSIGNMENT

INVENTOR AND CITY	Whereas, I, JONGOH KIM of 5337, NW Paseo Ter. Portland, Oregon 97229, USA
	have invented:
TITLE:	HIGH VOLTAGE FIELD BALANCE METAL OXIDE FIELD EFFECT TRANSISTOR (FBM)
DATE INVENTOR	and executed a United States patent application therefor
SIGNED THE DECLARATION	on J <sub>1</sub> / <sub>2</sub> 27th, 2012. Said assignor hereby authorize and request their attorney, Joshua D. Isenberg, of 809 Corporate Way, Fremont, California, to insert here in parentheses (Application number 13/561,523, filed July 30, 2012) the filing date and application number of said application when known.
	Whereas, Alpha and Omega Semiconductor Incorporated, a California Corporation, having its registered address at 475 Oakmead Pkwy, Sunnyvale, CA 94085, (hereinafter called AOS), desires to acquire the entire right, title and interest of said application and invention, and to any United States and foreign patents to be obtained therefore;
	Now therefore for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the invention set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by
CITY AND	Signed and Sealed at Sunnyvale, CA on July/25th , 2012
DATE	on <u>July/25th</u> , 2012

Jongoh Kim

Jongoh Kim

Docket No.: ANO-056/US Assignment

ANO-056Attorney Docket No: ANO-056/US

### T

	ASSIGNMENT
INVENTOR AND CITY	Whereas, I, YONGPING DING of 1246 San Moritz Dr. San Jose, CA 95132, USA
	have invented:
TITLE:	HIGH VOLTAGE FIELD BALANCE METAL OXIDE FIELD EFFECT TRANSISTOR (FBM)
DATE INVENTOR SIGNED THE DECLARATION	and executed a United States patent application therefor  on
	Whereas, Alpha and Omega Semiconductor Incorporal California Corporation, having its registered address at 475 Oar Pkwy, Sunnyvale, CA 94085, (hereinafter called AOS), desires to a the entire right, title and interest of said application and invention, any United States and foreign patents to be obtained therefore:

aid assignor hereby authorize and request iberg, of 809 Corporate Way, Fremont, in parentheses (Application number July 30, 2012 ) the filing said application when known. Omega Semiconductor Incorporated, a its registered address at 475 Oakmead hereinafter called AOS), desires to acquire t of said application and invention, and to ates and foreign patents to be obtained therefore; Now therefore for a valuable consideration, receipt whereof is hereby acknowledged, I, the above named, hereby sell, assign, and transfer to AOS, its successors and assigns, the entire right, title and interest in the said application and invention therein disclosed for the United States and foreign countries, and all rights of priority resulting from the filing said United States application, and I request the Commissioner of Patents to issue any Letters Patent granted upon the invention set forth in said application to AOS its successors and assigns; and I hereby agree that AOS may apply for foreign Letters Patent on said invention and I will execute all papers necessary in connection with the United States and foreign applications when called upon to do so by Signed and Sealed at Sunnyvale, CA

Docket No.: ANO-056/US

CITY AND

DATE

Assignment

**PATENT REEL: 028678 FRAME: 0066** 

RECORDED: 07/30/2012